



Docket No.: 206169US99

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313



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SIR:

Attached hereto for filing are the following papers:

SUPPLEMENTAL AMENDMENT W/MARKED-UP COPY

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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EXAMINER: BAUMEISTER

GROUP ART UNIT: 2815



DOCKET NO.: 206169US99
IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF
JAMAL RAMDANI ET AL
SERIAL NO: 09/766,046
FILED: JANUARY 19, 2001

STRUCTURE AND METHOD FOR
FABRICATING GAN DEVICES
UTILIZING THE FORMATION OF
A COMPLIANT SUBSTRATE

SUPPLEMENTAL AMENDMENT
COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Office Communication dated May 12, 2003, please amend the
above-identified application as follows.

IN THE CLAIMS

Please amend Claim 9 as follows.

--9. (Amended) The semiconductor structure of Claim 8, wherein the Zintl-type
phase material comprises at least one of SrAl₂, SrAl₄ (MgCaYb)Ga₂, (Ca, Sr, Eu, Yb)In₂,
BaGe₂As, and SrSn₂As₂.--

SUPPORT FOR AMENDMENT

C
Applicants appreciate the close review of their response filed March 3, 2003, and